WILLAS

RoHS COMPLIANT

SOT-23 Plastic-Encapsulate Diodes

MMBD2004S

SWITCHING DIODE

FEATURES

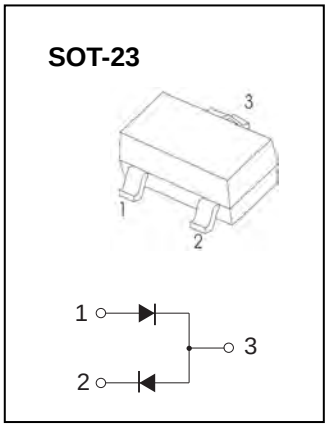
MMBD2004S type is a silicon switching dual in series diode manufactured by the epitaxial planar process, designed for applications requiring high voltage capability. Power dissipation

Pb-Free package is available

RoHS product for packing code suffix "G"

Halogen free product for packing code suffix "H"

Moisture Sensitivity Level 1



MARKING : B6D

Maximum Ratings @Ta=25℃

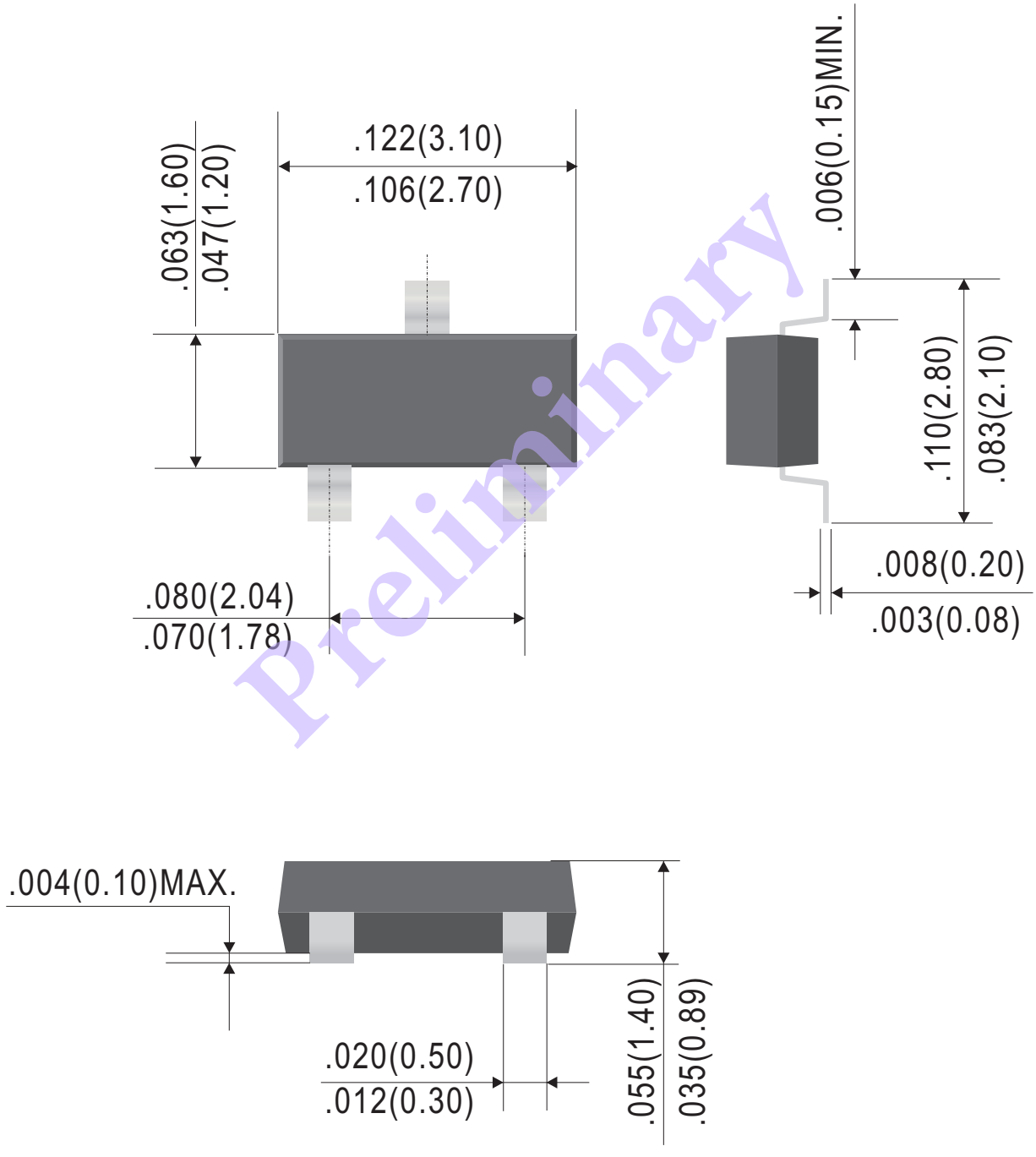
Parameter	Symbol	Limit	Unit
Non-Repetitive Peak Reverse Voltage	V_{RM}	300	V
DC Blocking Voltage	V_R	240	V
Peak Repetitive Current	I_O	200	mA
Continuous Forward Current	I_F	225	mA
Peak Repetitive Forward Current	I_{FRM}	625	mA
Forward Surge Current t=1μs	I_{FSM}	4.0	A
Forward Surge Current t=1s	I_{FSM}	1.0	A
Power Dissipation	Pd	250	mW
Junction Temperature	T_J	150	℃
Storage Temperature Range	T_{STG}	-55~+150	℃

ELECTRICAL CHARACTERISTICS (Ta=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Max	Unit
Reverse breakdown voltage	$V_{(BR)}$	I_R= 100μA	240		V
Reverse voltage leakage current	I_R	V_R=240V		0.1	μA
Forward voltage	V_F	I_F=100mA		1	V
Diode capacitance	C_D	V_R=0V f=1MHz		5	pF
Reveres recovery time	t_{rr}	I_F=I_R=30mA,R_L=100Ω		50	ns

Outline Drawing

SOT-23



Dimensions in inches and (millimeters)

Rev.D